

## **Product Description**

The PE4135 is a high linearity passive Quad MOSFET Mixer for GSM800 & Cellular Base Station Receivers, exhibiting high dynamic range performance over a broad LO drive range of up to 20 dBm. This mixer integrates passive matching networks to provide single-ended interfaces for the RF and LO ports, eliminating the need for external RF baluns or matching networks. The PE4135 is optimized for frequency downconversion using low-side LO injection for GSM800 & Cellular Base Station application, and is also suitable for up-conversion applications.

The PE4135 is manufactured on Peregrine's UltraCMOS<sup>™</sup> process, a patented variation of silicon-on-insulator (SOI) technology on a sapphire substrate, offering the performance of GaAs with the economy and integration of conventional CMOS.

### High Linearity UltraCMOS™ Quad MOSFET Mixer

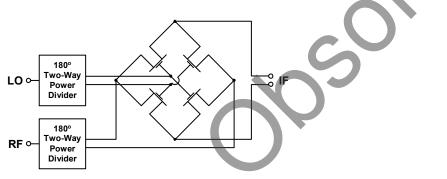
### Features

- Integrated, single-ended RF & LO interfaces
- High linearity: Typical IIP3 at 32dBm 820 - 920 MHz (+17 dBm LO)
- Low conversion loss: 6.8 dB (+17 dBm LO)
- High isolation: Typical LO-IF at 42 dB, LO-RF at 32 dB
- Small 6-lead 3x3 mm DFN package

### Figure 1. Functional Diagram

## Figure 2. Package Type

6-lead DFN





### Table 1. Electrical Specifications @ +25 °C (unless otherwise specified)

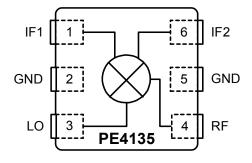
| Parameter <sup>1</sup>       | Minimum | Typical | Maximum | Units |
|------------------------------|---------|---------|---------|-------|
| Frequency Range:             |         |         |         |       |
| LO                           | 750     |         | 850     | MHz   |
| RF                           | 820     |         | 920     | MHz   |
| IF <sup>2</sup>              |         | 70      |         | MHz   |
| Conversion Loss <sup>3</sup> |         | 6.8     | 7.3     | dB    |
| Isolation:                   |         |         |         |       |
| LO-RF                        | 30      | 32      |         | dB    |
| LO-IF                        | 40      | 42      |         | dB    |
| Input IP3                    | 29      | 32      |         | dBm   |
| Input 1 dB Compression       |         | 21      |         | dBm   |

Notes: 1. Test conditions unless otherwise noted: IF = 70 MHz, LO input drive = 17 dBm, RF input drive = 3 dBm.

- 2. An IF frequency of 70 MHz is a nominal frequency. The IF frequency can be specified by the user as long as the RF and LO frequencies are within the specified maximum and minimum.
- 3. Conversion Loss includes loss of IF transformer (M/A COM ETC1-1-13, nominal loss 0.7 dB at 70 MHz).



## Figure 3. Pin Configuration (Top View)



### Table 2. Pin Descriptions

| Pin<br>No. | Pin<br>Name | Description   |  |
|------------|-------------|---|--|
| 1          | IF1         | IF differential output.   |  |
| 2          | GND         | Ground connections for Mixer. Traces<br>should be physically short and connect<br>immediately to ground plane for best<br>performance. The exposed solder pad must<br>also be soldered to the ground plane for<br>best performance. |  |
| 3          | LO          | LO Input.   |  |
| 4          | RF          | RF Input.   |  |
| 5          | GND         | Ground connections for Mixer. Traces<br>should be physically short and connect<br>immediately to ground plane for best<br>performance. The exposed solder pad must<br>also be soldered to the ground plane for<br>best performance. |  |
| 6          | IF2         | IF differential output.   |  |

### Latch-Up Avoidance

Unlike conventional CMOS devices, UltraCMOS<sup>™</sup> devices are immune to latch-up.

### Table 3. Absolute Maximum Ratings

| Symbol          | Parameter/Conditions        | Min | Max | Units |
|-----------------|-----------------------------|-----|-----|-------|
| T <sub>ST</sub> | Storage temperature range   | -65 | 150 | °C    |
| T <sub>OP</sub> | Operating temperature range | -40 | 85  | °C    |
| PLO             | LO input power              |     | 20  | dBm   |
| P <sub>RF</sub> | RF input power              |     | 12  | dBm   |

Absolute Maximum Ratings are those values listed in the above table. Exceeding these values may cause permanent device damage. Functional operation should be restricted to the limits in the DC Electrical Specifications table. Exposure to absolute maximum ratings for extended periods may affect device reliability.

## Table 4. Electrostatic Discharge (ESD) Ratings

| ÷ •       |                            | • •      |           | •     |
|-----------|----------------------------|----------|-----------|-------|
| Model     | Parameter/Conditions       | Min      | Max       | Units |
| НВМ1      | All Pins                   |          | 250       | V     |
| Notes: 1. | Human Body Model ESD Volta | age (HBM | , MIL_STI | D 883 |

1. Human Body Model ESD Voltage (HBM, MIL\_STD 883 Method 3015.7)

## Electrostatic Discharge (ESD) Precautions

When handling this UltraCMOS<sup>™</sup> device, observe the same precautions that you would use with other ESD-sensitive devices. Although this device contains circuitry to protect it from damage due to ESD, precautions should be taken to avoid exceeding the specified rating.

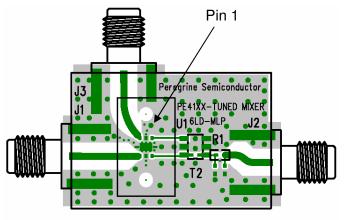
### **Moisture Sensitivity Level**

The Moisture Sensitivity Level rating for the PE4135 in packaging is MSL1.



## **Evaluation Kit**

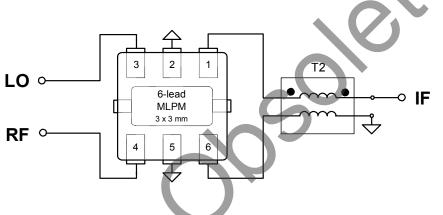
## Figure 4. Evaluation Board Layout



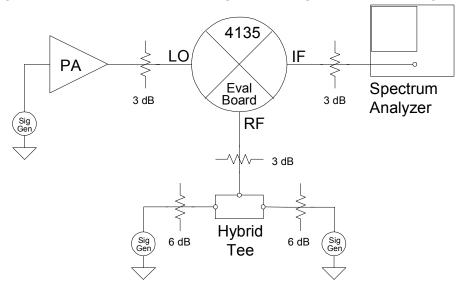
## Table 5. Bill of Materials

| Reference  | Value / Description |  |  |
|------------|---------------------|--|--|
| T2         | M/A Com ETK1-1-13   |  |  |
| R1         | 0Ω                  |  |  |
| U1         | PE4135 MLP Mixer    |  |  |
| J1, J2, J3 | SMA Connector       |  |  |

Figure 5. Evaluation Board Schematic



## Figure 6. Evaluation Board Testing Block Diagram, 2-Tone Setup

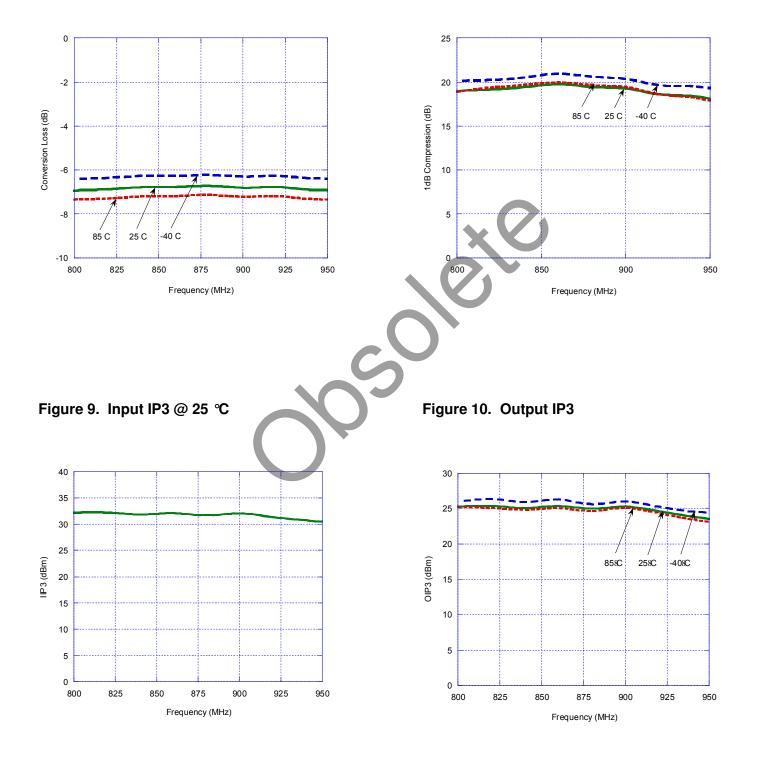




## Typical Performance Data (LO=17 dBm, RF=3 dBm, IF=70 MHz, unless otherwise specified)

## Figure 7. Conversion Loss





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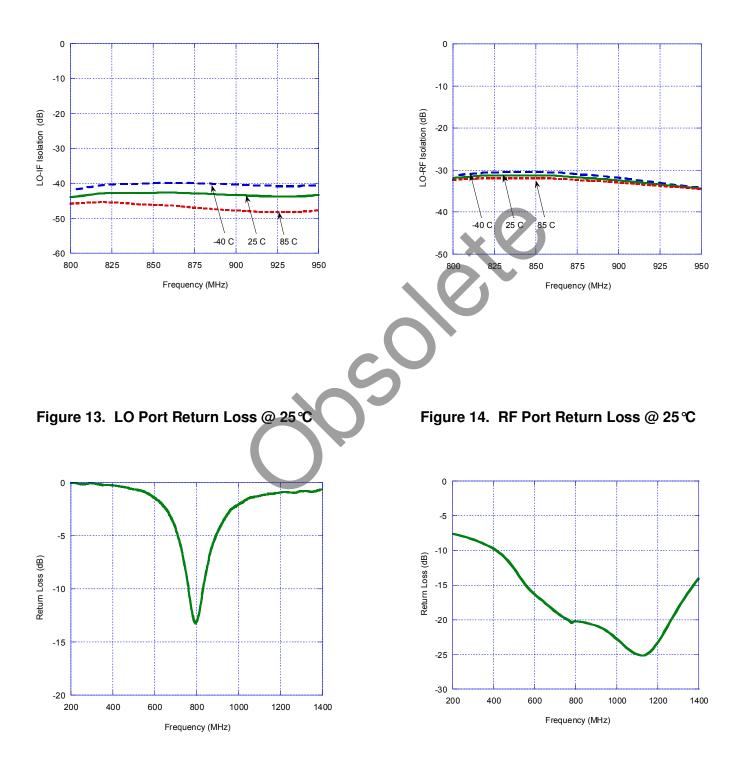




## Typical Performance Data (LO=17 dBm, RF=3 dBm, IF=70 MHz, unless otherwise specified)

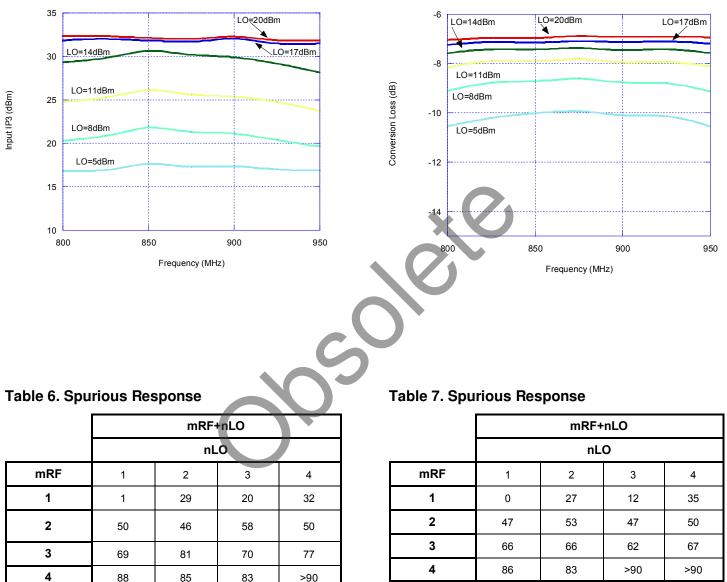
## Figure 11. LO-IF Isolation

Figure 12. LO-RF Isolation





# Typical Performance Data (LO=17 dBm, RF=3 dBm, IF=70 MHz, unless otherwise specified)Figure 15. Input IP3 Across LO PowerFigure 16. Conversion Loss Across LO Power



Note: Normalized to dB below PIF

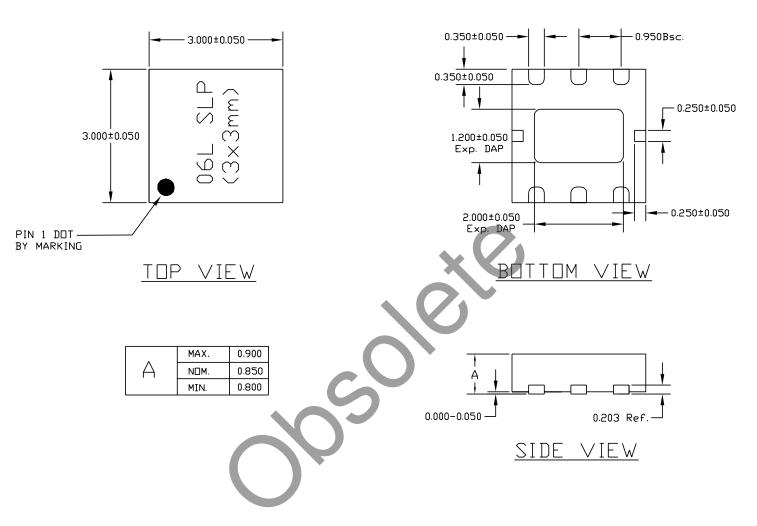
(RF=870 Mhz @ 3 dBm, LO=940 MHz @ 17 dBm)

Note: Normalized to dB below PIF (RF=870 Mhz @ 3 dBm, LO=940 MHz @ 17 dBm)



## Figure 17. Package Drawing

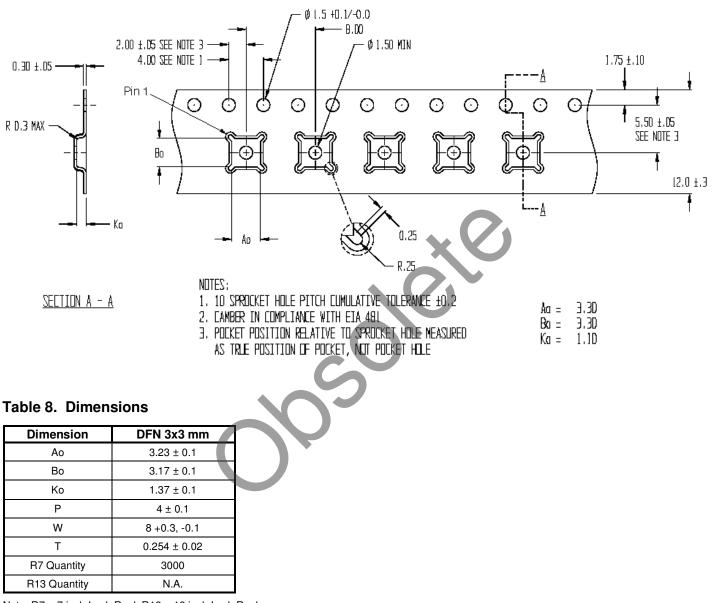
6-lead DFN





## Figure 18. Tape and Reel Specifications

6-lead DFN



## Note: R7 = 7 inch Lock Reel, R13 = 13 inch Lock Reel

### **Table 9. Ordering Information**

| Order Code     | Part Marking | Description                       | Package           | Shipping Method      |
|----------------|--------------|-----------------------------------|-------------------|----------------------|
| PE4135MLAB_CB  | 4135         | PE4135-06L Green DFN 3x3mm-12800F | 6-lead 3x3 mm DFN | 12800 units/Canister |
| PE4135MLAB-CBZ | 4135         | PE4135-06L Green DFN 3x3mm-3000C  | 6-lead 3x3 mm DFN | 3000 units/T&R       |
| EK4135-01      | PE4135-EK    | PE4135-06L Green DFN 3x3mm-EK     | Evaluation Kit    | 1/Box                |

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## **Data Sheet Identification**

### Advance Information

The product is in a formative or design stage. The data sheet contains design target specifications for product development. Specifications and features may change in any manner without notice.

### **Preliminary Specification**

The data sheet contains preliminary data. Additional data may be added at a later date. Peregrine reserves the right to change specifications at any time without notice in order to supply the best possible product.

## **Product Specification**

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